

Docket No. 740756-2435

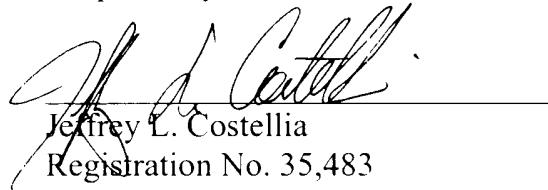
Serial No. 10/073,284

Page 13

independent claims 50 and 52 do not contain either of the steps of forming an anti-electrostatic layer over the resin insulating film of the elected second specie or the wiping of the electrode (anode) of the non-elected first specie. Claims 58-61 are linking claims examinable with either specie.

Consideration and allowance of the instant application are now respectfully requested.

Respectfully submitted,



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**MARKED UP VERSION**

**IN THE CLAIMS:**

Please amend the claims as follows:

50. (Amended) A method of manufacturing a device comprising the steps of: forming a thin film transistor formed over a substrate having an insulating surface; forming an interlayer insulating film over the thin film transistor; forming an electrode over the interlayer insulating film; forming a wiring line connecting the electrode [anode] with the thin film transistor, over the interlayer insulating film; forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

52. (Amended) A method of manufacturing a device comprising the steps of: forming a thin film transistor formed over a substrate having an insulating [25] surface; forming an interlayer insulating film over the thin film transistor; forming an electrode over the interlayer insulating film; forming a wiring line connecting the electrode [anode] with the thin film transistor, over the interlayer insulating film; forming a resin insulating film over the anode, the wiring line and the interlayer insulating film; forming a film for preventing the substrate over which the thin film transistor is

formed from a contamination and an electrostatic discharge damage.

54. (Amended) A method of manufacturing a device according to claim 52, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material [comprises] selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [[hydroxyalkyl monoethanolamine]], N,N-Bis(2-hydroxyethyl)alkylamine [[alkyl diethanolamine]], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

55. (Amended) A method of manufacturing a light emitting device according to claim 54, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material [is] formed by spin coating or evaporation.

56. (Amended) A method of manufacturing a light emitting device according to claim 52, wherein the film for preventing the substrate from contamination and electrostatic discharge damage comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

57. (Amended) A method of manufacturing a light emitting device according to claim 53 [52], wherein the method further comprises the steps of removing the film,

etching the resin insulating film to form a bank, wiping the anode, forming an organic compound layer over the bank and the anode.

59. (Amended) A method of manufacturing a device according to claim 58, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material [comprises] selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl [10] ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine [[hydroxyalkyl monoethanolamine]], N,N-Bis(2-hydroxyethyl)alkylamine [[alkyl diethanolamine]], alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.